

D1
level

forming a lower electrode layer of said ferroelectric capacitor over said insulation film;

forming a ferroelectric film on said lower electrode as a capacitor insulation film of said ferroelectric capacitor;

crystallizing said ferroelectric film by applying a thermal annealing process in an O₂ atmosphere under a reduced total pressure in the range between 1 Torr and 40 Torr; and

forming an upper electrode layer on said ferroelectric film.

14. (Amended) A method of fabricating a semiconductor device having a ferroelectric capacitor, comprising the steps of:

forming an active device element on a substrate;

forming an insulation film over said substrate to cover said active device element;

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forming a lower electrode layer of said ferroelectric capacitor over said insulation film, said lower electrode layer including a layer part containing Ti atoms;

forming a ferroelectric film on said lower electrode layer as a capacitor insulation film of said ferroelectric capacitor;

crystallizing said ferroelectric film by applying a thermal annealing process in an atmosphere of an oxidizing gas with a fraction of 1 to 20% in volume; and

forming an upper electrode layer on said ferroelectric film,

wherein said step of crystallizing said ferroelectric film is conducted by supplying O₂ controlled to cause an oxidation in said Ti atoms reached a surface of said lower electrode from said layer part containing Ti atoms.

15. (Thrice Amended) A semiconductor device, comprising:

a substrate;

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an active device element formed on said substrate;

an insulation film provided over said substrate to cover said active device element;